

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

A metal oxide semiconductor transistor includes a semiconductor substrate; a source area ~~formed~~ located in a device area of the semiconductor substrate; a drain area ~~formed~~ located in the device area; a gate layer ~~formed~~ located on and across the device area between the source area and the drain area; a control gate layer; and a diffusion area ~~formed~~ located in the device area, between the gate area and the control gate area. The control gate layer has a first part including a first end of the control gate layer and a second part including a second end of the control gate layer. The first part is ~~formed~~ located on the device area between the source area and the gate layer. ~~The first end is disposed so that there~~ There is a gap between the first end and an edge of the device area.